



# Laser Diode

## FJLD-100S-660-TO56-60TX

### DESCRIPTION

The **FJLD-100S-660-TO56-60TX** is a 660 nm 100mW quantum well semiconductor laser designed for high output power application. The laser diode is supplied in TO-56 housing with the monitor PD and hermetically sealed with the flat glass cap.

### ABSOLUTE MAXIMUM RATING

(CW operation,  $T_c = 25^\circ\text{C}$ )

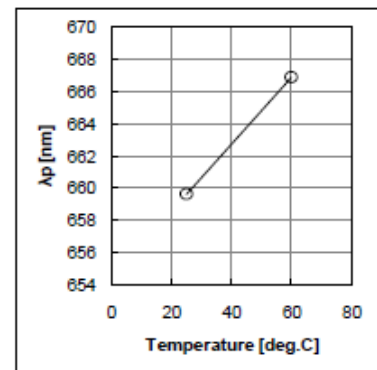
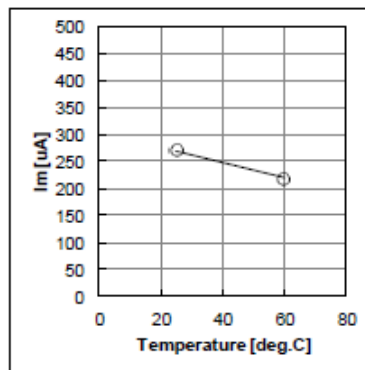
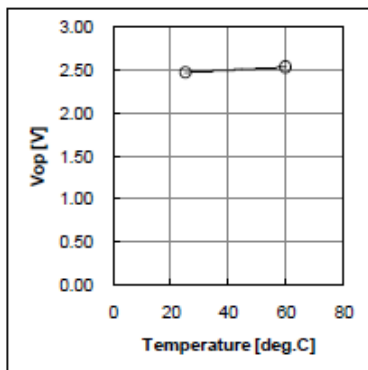
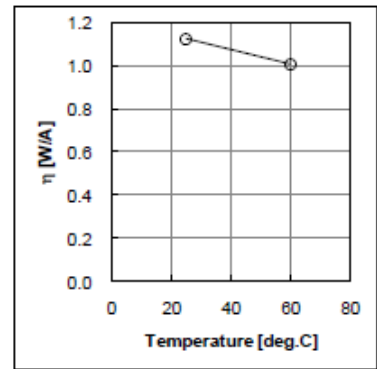
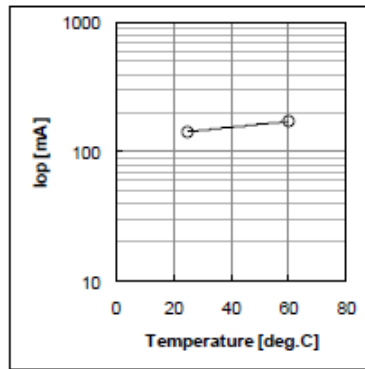
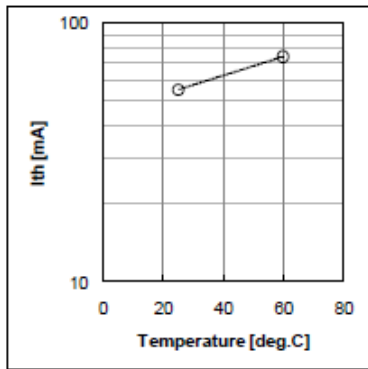
PARAMETER	SYMBOL	VALUE	UNIT
Optical output power	$P_o$	130	mW
LD reverse voltage	$V_{RLD}$	2	V
PD reverse voltage	$V_{RPD}$	30	V
Operation temperature	$T_c$	-10 to 60	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-40 to 85	$^\circ\text{C}$

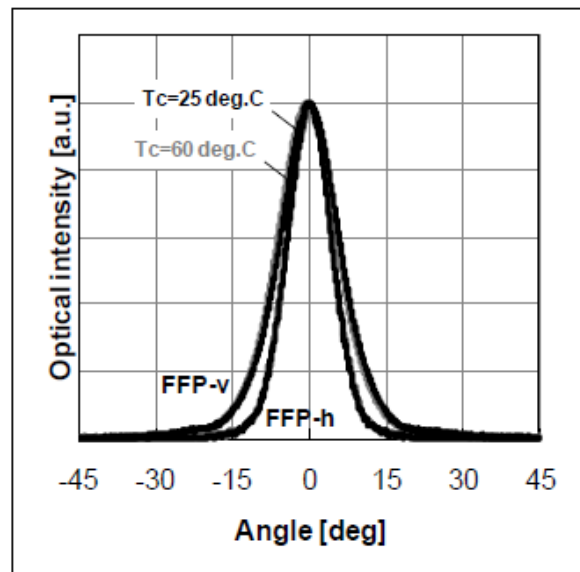
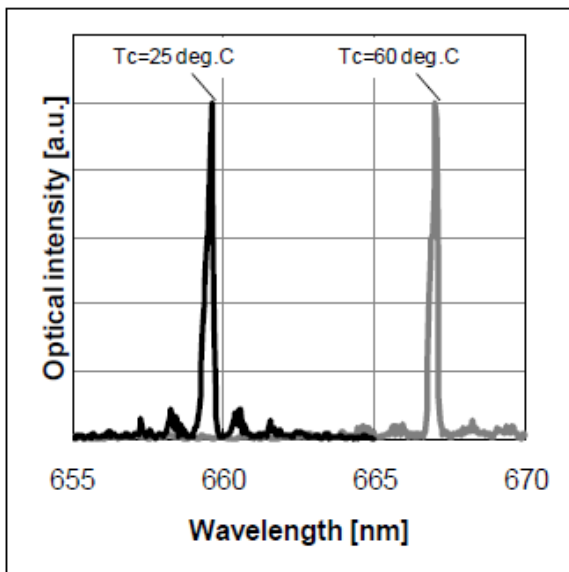
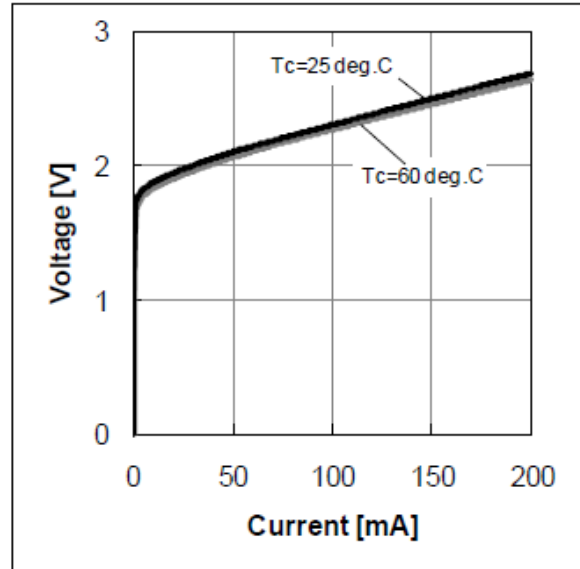
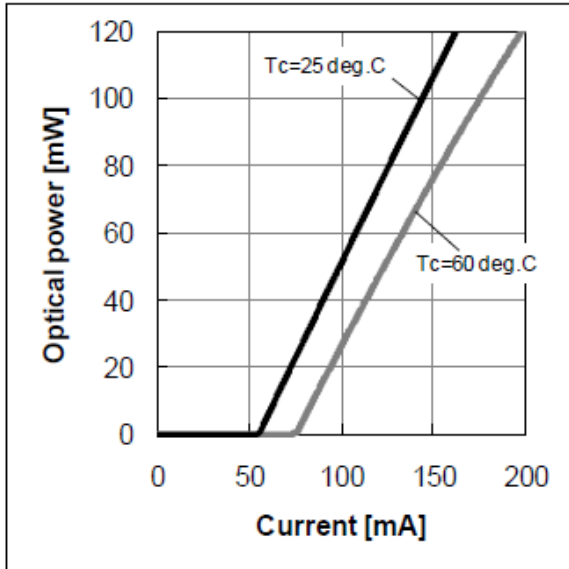
X – electrical contact type ( N, P )

## OPTICAL AND ELECTRICAL CHARACTERISTICS

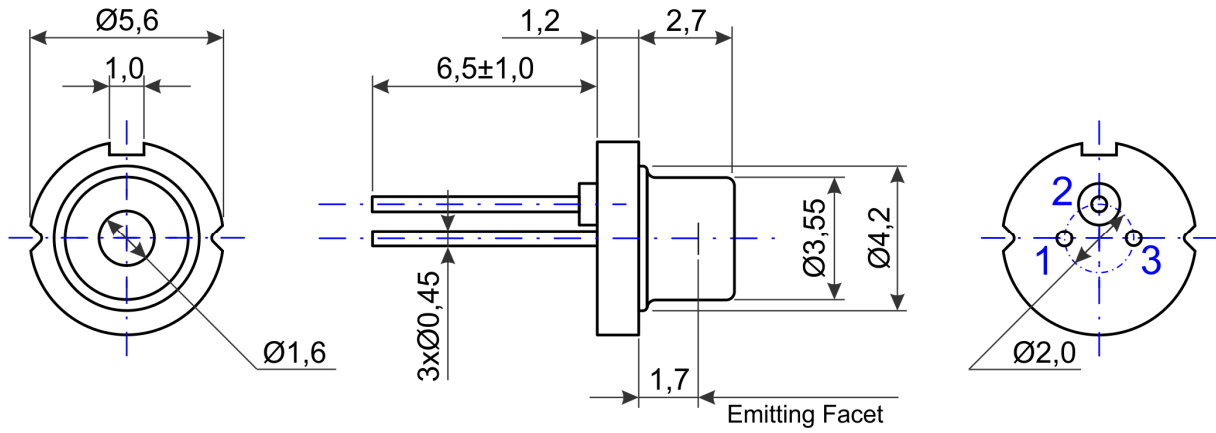
( $T_c = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Threshold current	$I_{th}$	CW	-	55	70	mA
Operation current	$I_{op}$	CW, $P_o=100\text{ mW}$	-	145	200	mA
Operation voltage	$V_{op}$	CW, $P_o=100\text{ mW}$	-	2.5	3.0	V
Slope efficiency	$\eta$	CW, $P_o=5 - 100\text{ mW}$	0.8	1.1	-	W/A
Monitor current	$I_m$	CW, $P_o=100\text{ mW}$ , $V_{RD}=5\text{ V}$	50	300	600	$\mu\text{A}$
Peak wavelength	$\lambda_p$	CW, $P_o=100\text{ mW}$	655	660	665	Nm
Far filed pattern horizontal	$\theta_h$	CW, $P_o=100\text{ mW}$	-	10	-	deg.
Far filed pattern vertical	$\theta_v$	CW, $P_o=100\text{ mW}$	-	14	-	deg.

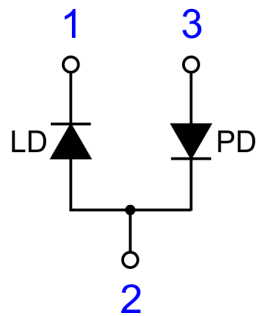




**PACKAGE DRAWING**



N-type



P-type

